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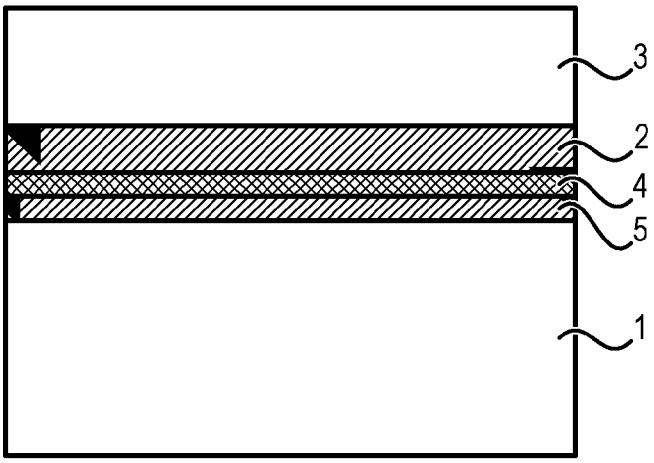
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(54) **Title**: MANUFACTURING METHOD FOR A SEMICONDUCTOR ON INSULATOR TYPE SUBSTRATE FOR RADIOFREQUENCY APPLICATIONS

FIG. 3



(57) **Abstract**: The invention relates to a method for manufacturing a semiconductor on insulator type substrate for radiofrequency applications, comprising the following steps in sequence: (a) provision of a silicon substrate (1) with an electrical resistivity of more than 500 Ohm. cm, (b) formation of a polycrystalline silicon layer (4) on said substrate (1), said method comprising a step between steps a) and b) to form a dielectric material layer (5), different from a native oxide layer, on the substrate (1), between 0.5 and 10 nm thick.

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